Preferred Device

# **Silicon Controlled Rectifiers**

# **Reverse Blocking Thyristors**

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supply crowbar circuits.

- Glass Passivated Junctions with Center Gate Fire for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Constructed for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- 80 A Surge Current Capability
- Insulated Package Simplifies Mounting
- N Indicates UL Registered File #E69369
- Device Marking: Logo, Device Type, e.g., MCR218-6, Date Code

## MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open)  MCR218-6FP	V <sub>DRM</sub> , V <sub>RRM</sub>	400	Volts
MCR218-10FP		800	S
On-State RMS Current (T <sub>C</sub> = +70°C) <sup>(2)</sup> (180° Conduction Angles)	I <sub>T(RMS)</sub>	8.0	Amps
Peak Nonrepetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T <sub>J</sub> = 125°C)	I <sub>TSM</sub>	100	Amps
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	26	A <sup>2</sup> s
Forward Peak Gate Power $(T_C = +70^{\circ}C, \text{ Pulse Width} \leq 1.0 \mu\text{s})$	Р <sub>GМ</sub>	5.0	Watts
Forward Average Gate Power (T <sub>C</sub> = +70°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.5	Watt
Forward Peak Gate Current $(T_C = +70^{\circ}C, \text{ Pulse Width } \leq 1.0 \mu\text{s})$	I <sub>GM</sub>	2.0	Amps
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity ≤ 20%) (93)	V <sub>(ISO)</sub>	1500	Volts
Operating Junction Temperature	TJ	–40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	−40 to +150	°C

- (1) V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
- (2) The case temperature reference point for all T<sub>C</sub> measurements is a point on the center lead of the package as close as possible to the plastic body.



## ON Semiconductor

http://onsemi.com

ISOLATED SCRs (%) 8 AMPERES RMS 400 thru 800 VOLTS





ISOLATED TO-220 Full Pack CASE 221C STYLE 2

PIN ASSIGNMENT			
1	Cathode		
2	Anode		
3	Gate		

#### **ORDERING INFORMATION**

Device	Package	Shipping
MCR218-6FP	ISOLATED TO220FP	500/Box
MCR218-10FP	ISOLATED TO220FP	500/Box

**Preferred** devices are recommended choices for future use and best overall value.

### THERMAL CHARACTERISTICS

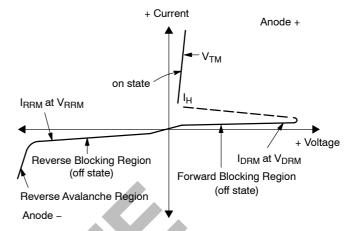
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	2	°C/W
Thermal Resistance, Case to Sink	R <sub>θCS</sub>	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

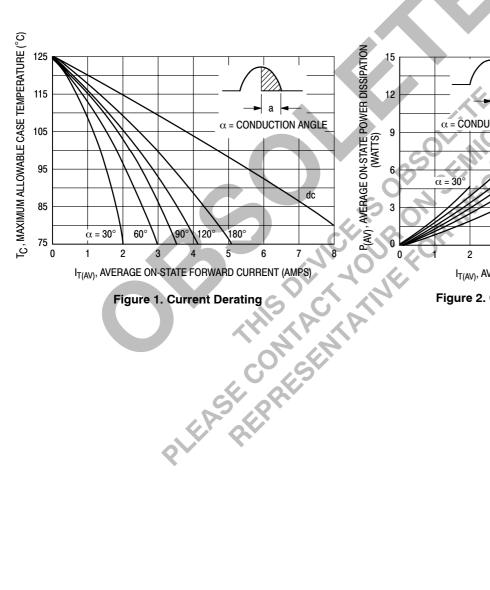
Characteristic	Symbol	Min	Тур	Max	Unit
	Symbol	IVIIII	тур	IVIAX	Offic
OFF CHARACTERISTICS	T	1	1	1	
Peak Repetitive Forward or Reverse Blocking Current $(V_D = Rated V_{DRM}, Gate Open)$ $T_J = 25^{\circ}C$	I <sub>DRM,</sub> I <sub>RRM</sub>	_	_	10	μΑ
T <sub>J</sub> = 125°C		_	_	2	mA
ON CHARACTERISTICS					
Peak Forward On-State Voltage <sup>(1)</sup> (I <sub>TM</sub> = 16 A Peak)	V <sub>TM</sub>	_	1	1,8	Volts
Gate Trigger Current (Continuous dc) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	I <sub>GT</sub>	_	10	25	mA
Gate Trigger Voltage (Continuous dc) (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms)	V <sub>GT</sub>	-3	2	1.5	Volts
Gate Non-Trigger Voltage (V <sub>AK</sub> = 12 Vdc, R <sub>L</sub> = 100 Ohms, T <sub>J</sub> = 125°C)	V <sub>GD</sub>	0.2		_	Volts
Holding Current (V <sub>AK</sub> = 12 Vdc, Initiating Current = 200 mA, Gate Open)	BHIN	PIN	16	30	mA
Turn-On Time (I <sub>TM</sub> = 8 A, I <sub>GT</sub> = 40 mAdc)	t <sub>gt</sub>		1.5	_	μs
Turn-Off Time ( $V_D$ = Rated $V_{DRM}$ , $I_{TM}$ = 8 A, $I_R$ = 8 A) $I_J$ = 25°C $I_J$ = 125°C	ta	_ _	15 35	_ _	μS
DYNAMIC CHARACTERISTICS	4				
Critical Rate-of-Rise of Off-State Voltage (Gate Open, V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform)	dv/dt		100	_	V/μs
(Gate Open, V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform)  1) Pulse Test: Pulse Width = 1 ms, Duty Cycle ≤ 2%.					

<sup>(1)</sup> Pulse Test: Pulse Width = 1 ms, Duty Cycle ≤ 2%

## **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Off State Reverse Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Peak on State Voltage
I <sub>H</sub>	Holding Current





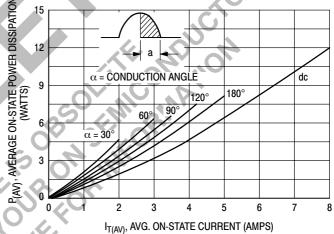


Figure 2. On-State Power Dissipation

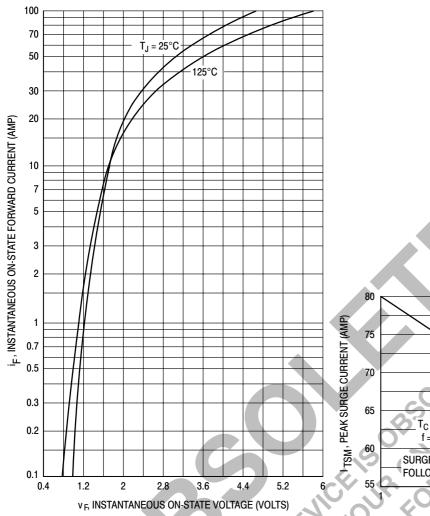


Figure 3. Maximum On-State Characteristics

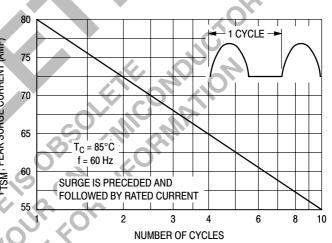


Figure 4. Maximum Non-Repetitive Surge Current

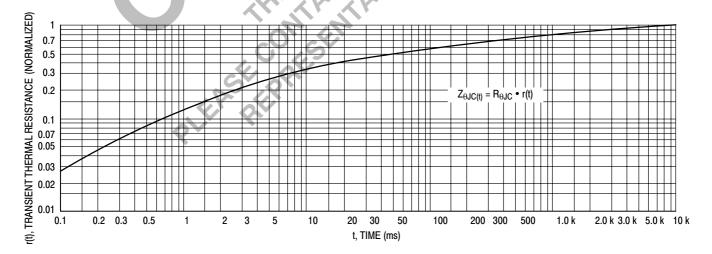
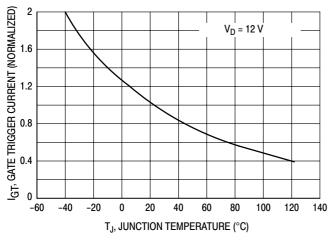


Figure 5. Thermal Response



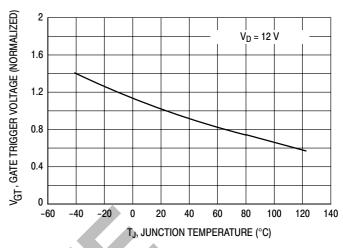
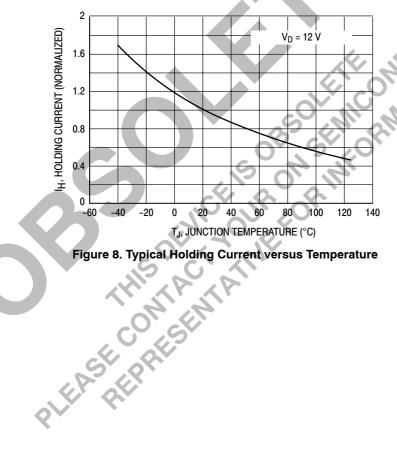


Figure 6. Typical Gate Trigger Current versus **Temperature** 

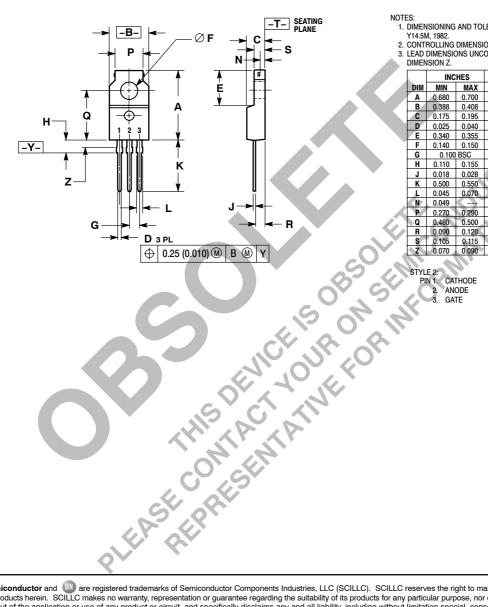
Figure 7. Typical Gate Trigger Voltage versus Temperature



#### PACKAGE DIMENSIONS

### ISOLATED TO-220 Full Pack

CASE 221C-02 **ISSUE C** 



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
  3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.680	0.700	17.28	17.78
В	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100	0.100 BSC		BSC
Н	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049	G-7	1.25	
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S 7	0.105	0.115	2.67	2.92
7	0.070	0.090	1 78	2 28

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